Central
Semiconductor Corp.
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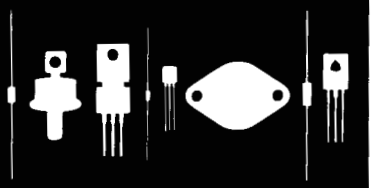
145 Adams Avenue
Hauppauge, New York 11788



1N4446 THRU 1N4449

SILICON SWITCHING DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N4446 series types are very high speed Silicon Switching Diodes designed for computer and general purpose applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Peak Working Reverse Voltage	V_{RWM}	75	V
Average Forward Current	I_O	150	mA
Forward Steady-State Current	I_F	200	mA
Peak Forward Surge Current (1.0μs pulse)	I_{FSM}	2000	mA
Power Dissipation	P_D	500	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 TO +200	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

		1N4446		1N4447		1N4448		1N4449		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
BV_R	I_R=5μA	75		75		75		75		V
BV_R	I_R=100μA	100		100		100		100		V
I_R	V_R=20V		25		25		25		25	nA
I_R	V_R=20V, T_A=100°C		-		-		3.0		3.0	μA
I_R	V_R=20V, T_A=150°C		50		50		50		50	μA
V_F	I_F=5.0mA	-	-	-	-	0.62	0.72	0.63	0.73	V
V_F	I_F=20mA		1.0		1.0		-		-	V
V_F	I_F=30mA		-		-		-		1.0	V
V_F	I_F=100mA		-		-		1.0		-	V
C_T	V_R=0, f=1.0 MHz		4.0		2.0		4.0		2.0	pF
t_{rr}	V_R=6.0V, I_F=10mA, I_{rr}=1.0mA, R_L=100Ω		4.0		4.0		4.0		4.0	nS
$V_{FM(REC)}$	I_F=50mA, R_L=50Ω		-		-		2.5		2.5	V

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